

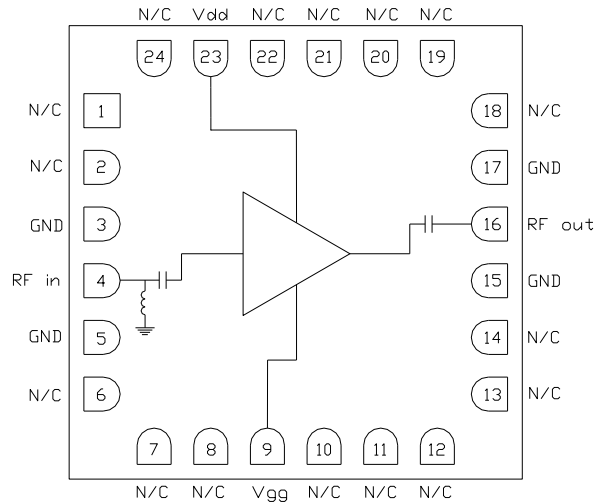
Features

- ▶ Wide bandwidth
- ▶ Low phase noise
- ▶ Low current consumption
- ▶ Pb-free RoHs compliant 4x4 mm SMT package

Description

The CMD245C4 is a wideband GaAs MMIC low phase noise amplifier housed in a leadless surface mount package that is ideally suited for military, space and communications systems. At 10 GHz the device delivers 18 dB of gain, a saturated output power of +21 dBm and a noise figure of 4.5 dB. Also with an input signal of 10 GHz the amplifier provides low phase noise performance of -165 dBc/Hz at 10 kHz offset. The CMD245C4 is a 50 ohm matched design which eliminates the need for RF port matching.

Functional Block Diagram



Electrical Performance – $V_{dd} = 5.0\text{ V}$, $V_{gg} = 3.0\text{ V}$, $T_A = 25\text{ }^\circ\text{C}$, $F = 10\text{ GHz}$

Parameter	Min	Typ	Max	Units
Frequency Range	5 – 20			GHz
Gain		18		dB
Input Return Loss		10		dB
Output Return Loss		12		dB
Noise Figure		4.5		dB
Output P1dB		18		dBm
Saturated Output Power		21		dBm
Phase Noise @ 10 kHz Offset		-165		dBc/Hz
Supply Current		76		mA

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Specifications

Absolute Maximum Ratings

Parameter	Rating
Drain Voltage, V _{dd}	8.0 V
Gate Voltage, V _{gg}	5.0 V
RF Input Power	+17 dBm
Channel Temperature, T _{ch}	150 °C
Power Dissipation, P _{diss}	602 mW
Thermal Resistance	108 °C/W
Operating Temperature	-40 to 85 °C
Storage Temperature	-55 to 150 °C

Operation of this device outside the maximum ratings may cause permanent damage.

Recommended Operating Conditions

Parameter	Min	Typ	Max	Units
V _{dd}	3.0	5.0	7.0	V
I _{dd}		76		mA
V _{gg}	0	3.0	4.0	V

Electrical performance is measured at specific test conditions. Electrical specifications are not guaranteed over all recommended operating conditions.

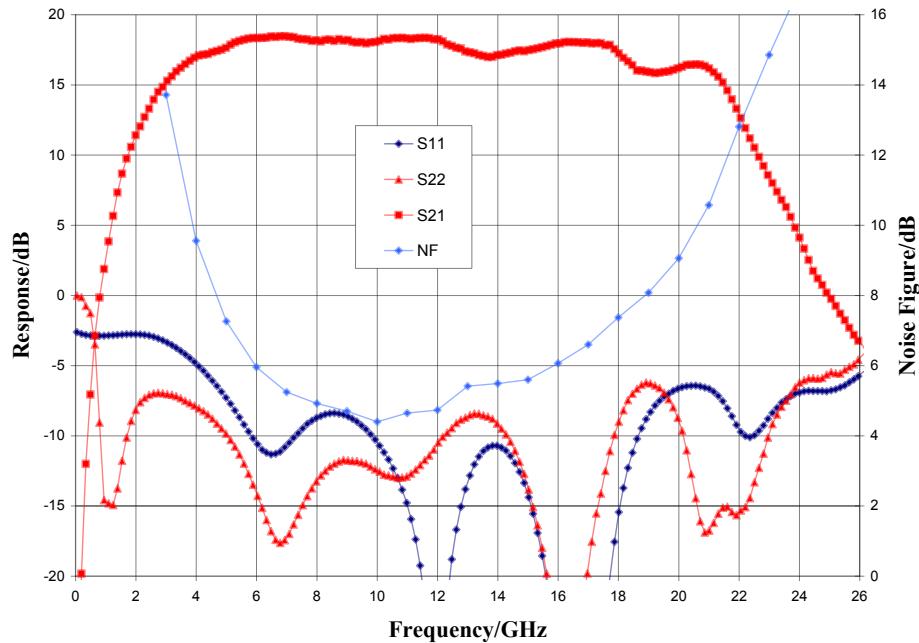
Electrical Specifications – V_{dd} = 5.0 V, V_{gg} = 3.0 V, T_A = 25 °C

Parameter	Min	Typ	Max	Min	Typ	Max	Units
Frequency Range	6 – 12			12 – 18			GHz
Gain	15	18	21.5	14	17.5	21.5	dB
Noise Figure		5			6		dB
Input Return Loss		10			15		dB
Output Return Loss		13			12		dB
Output P1dB	15	19		11	16		dBm
Saturated Output Power		21			20		dBm
Output IP3		29			29		dBm
Phase Noise @ 10 kHz Offset		-165			-165		dBc/Hz
Supply Current	53	76	100	53	76	100	mA

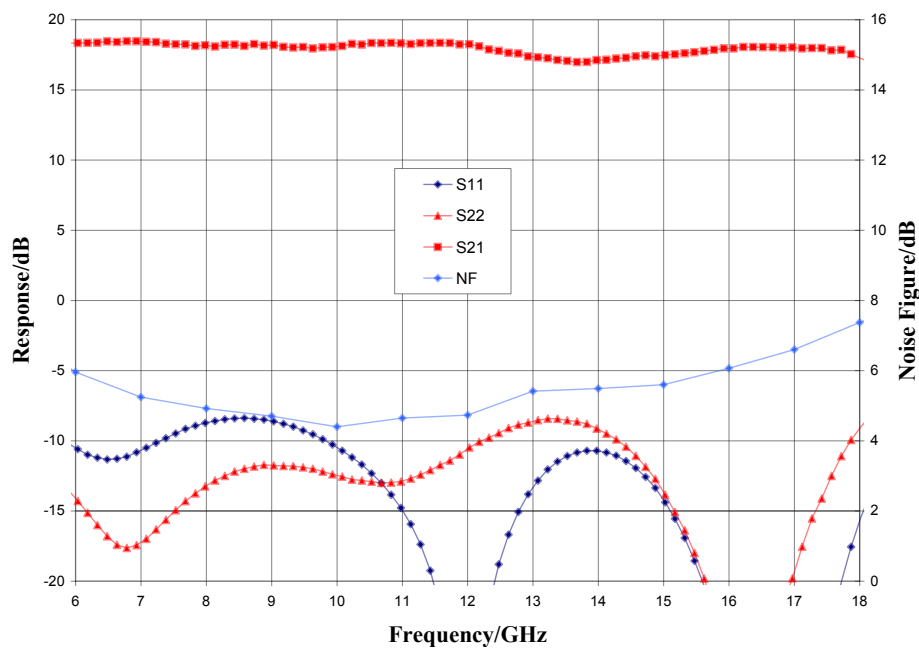
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Typical Performance

Broadband Performance, $V_{dd} = 5.0$ V, $V_{gg} = 3.0$ V, $I_{dd} = 76$ mA, $T_A = 25$ °C



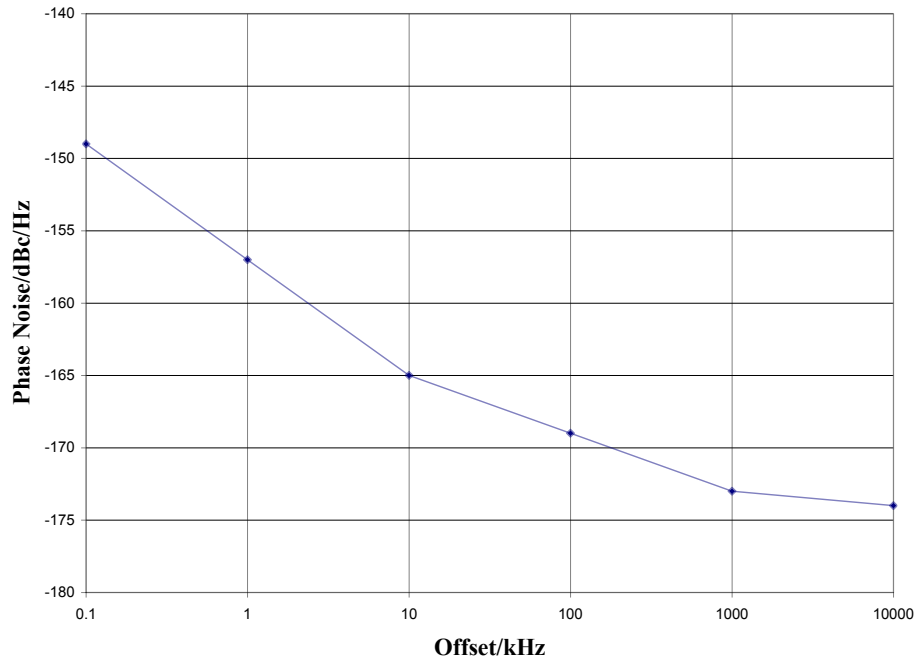
Narrow-band Performance, $V_{dd} = 5.0$ V, $V_{gg} = 3.0$ V, $I_{dd} = 76$ mA, $T_A = 25$ °C



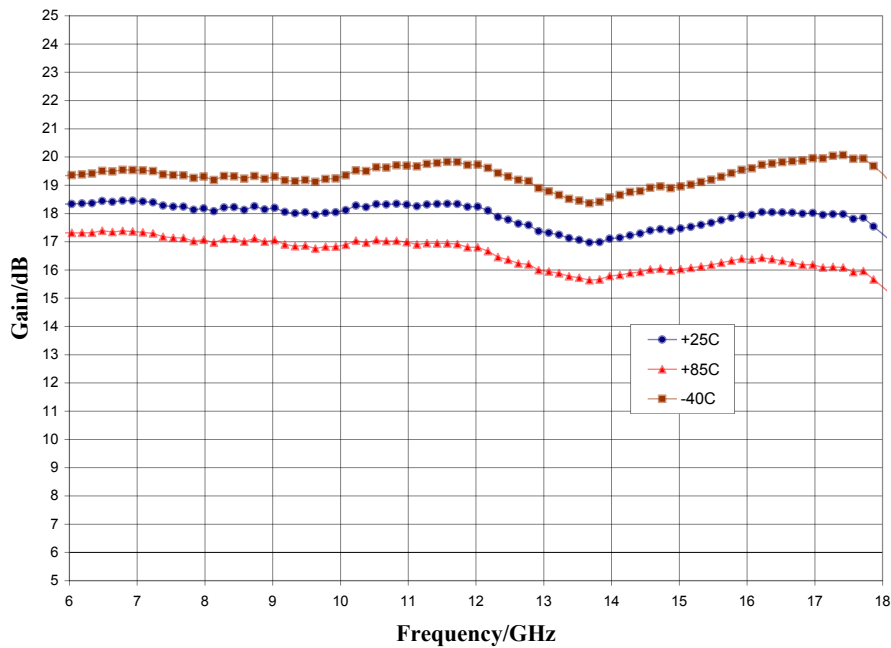
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Typical Performance

Additive Phase Noise @ P_{sat} , $V_{dd} = 5.0\text{ V}$, $V_{gg} = 3.0\text{ V}$, $T_A = 25\text{ }^\circ\text{C}$



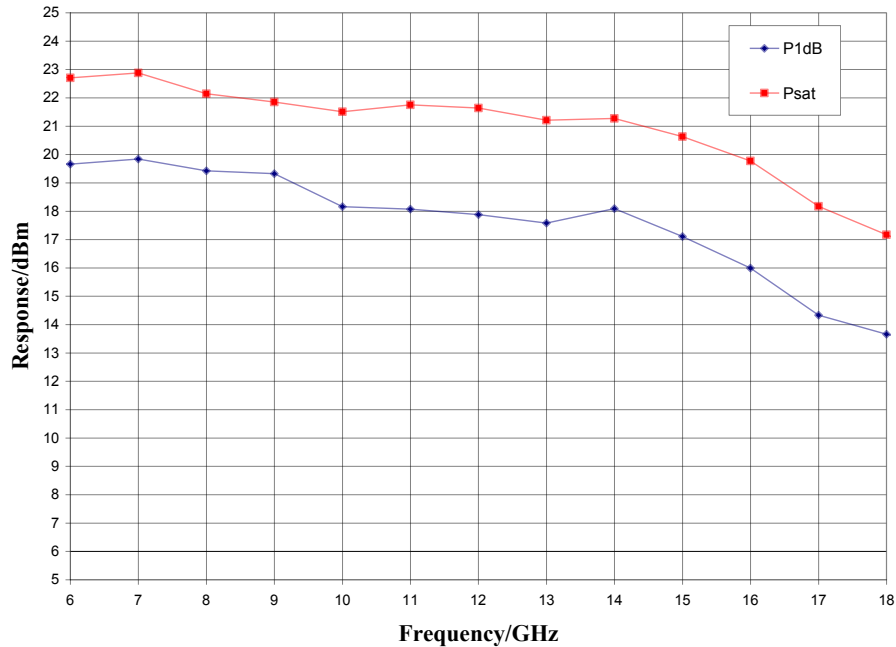
Gain vs. Temperature, $V_{dd} = 5.0\text{ V}$, $V_{gg} = 3.0\text{ V}$



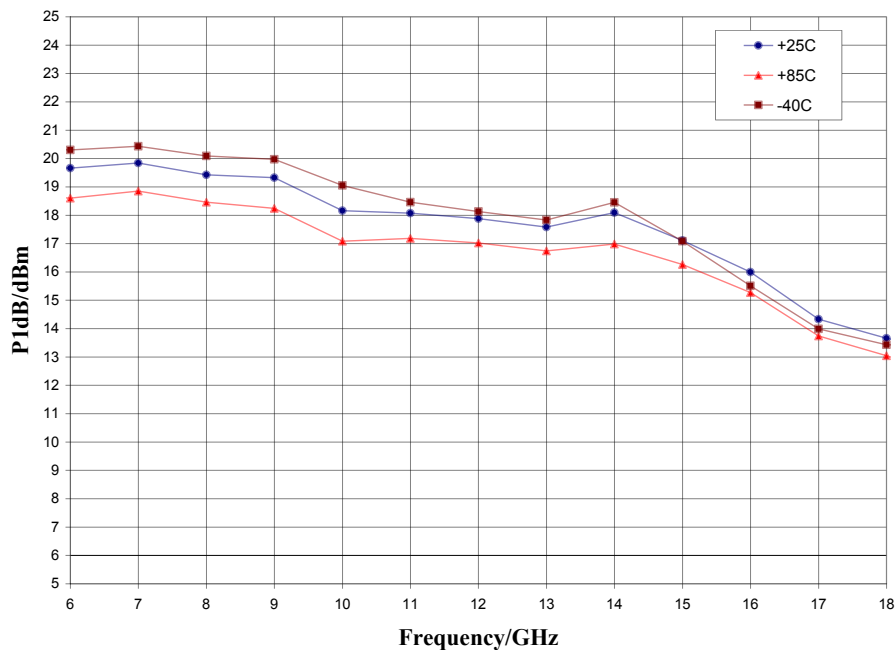
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Typical Performance

Output Power, $V_{dd} = 5.0\text{ V}$, $V_{gg} = 3.0\text{ V}$, $T_A = 25\text{ }^\circ\text{C}$

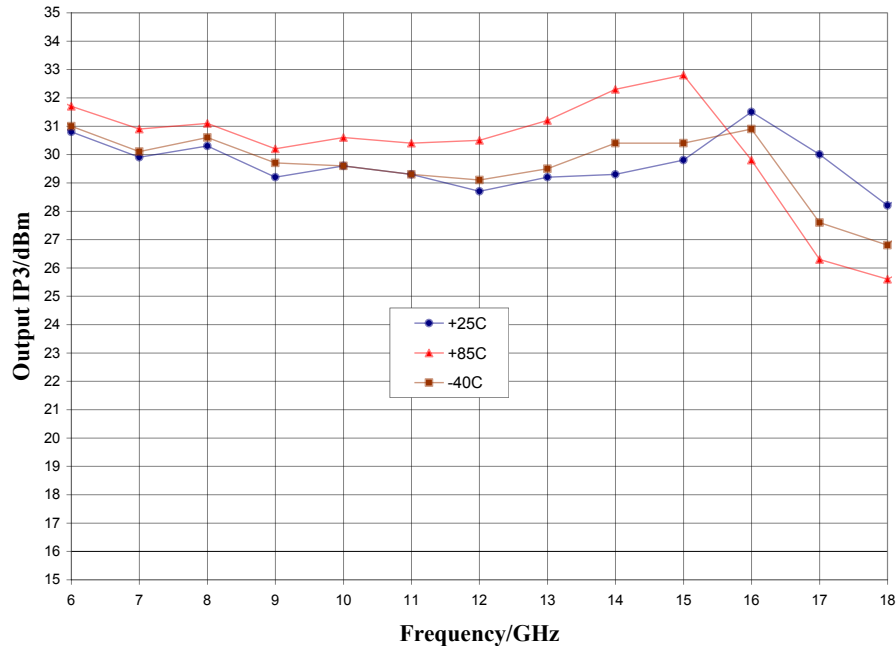


P1dB vs. Temperature, $V_{dd} = 5.0\text{ V}$, $V_{gg} = 3.0\text{ V}$

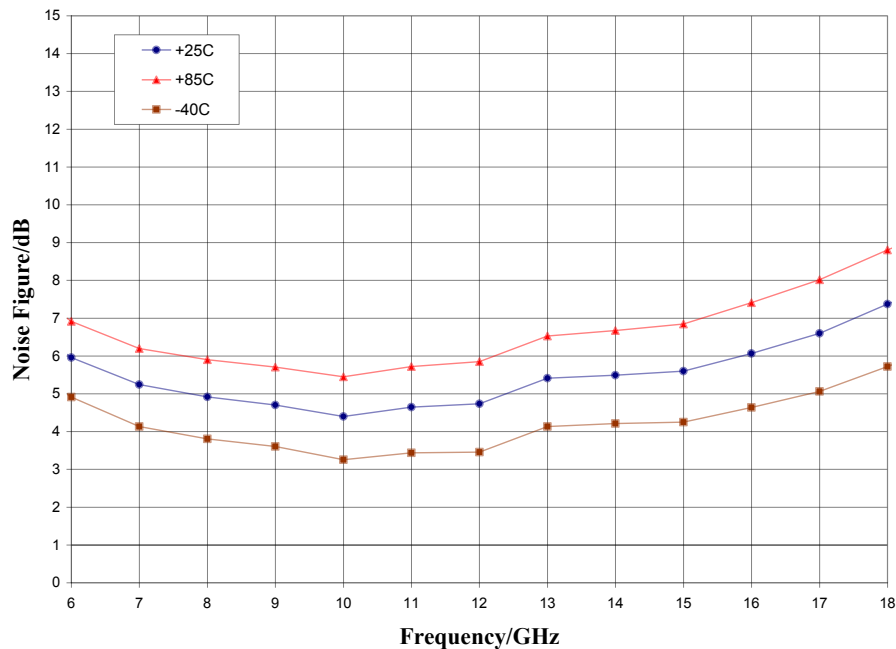


Typical Performance

Output IP3 vs. Temperature, $V_{dd} = 5.0\text{ V}$, $V_{gg} = 3.0\text{ V}$

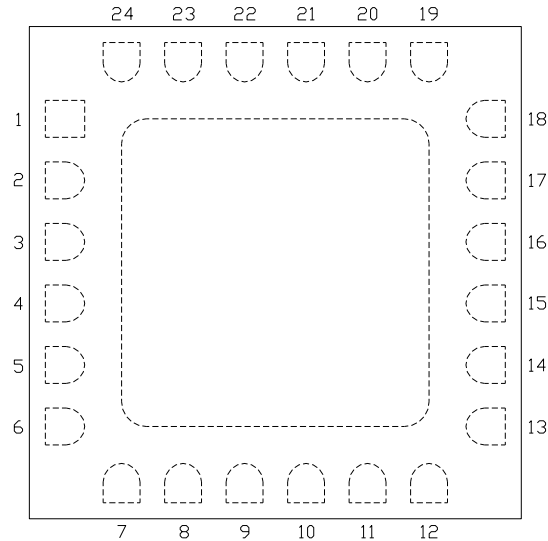


Noise Figure vs. Temperature, $V_{dd} = 5.0\text{ V}$, $V_{gg} = 3.0\text{ V}$


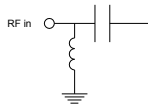
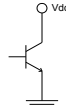

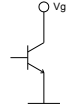


Pin Description

Pin Diagram



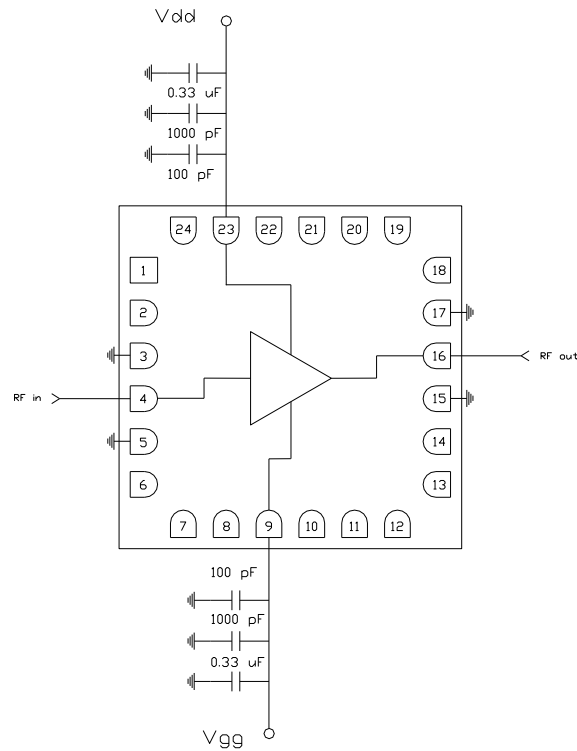
Functional Description

Pad	Function	Description	Schematic
1, 2, 6-8, 10-14, 18-22, 24	N/C	No connection required. These pins may be connected to RF/DC ground.	
3, 5, 15, 17 and die paddle	Ground	Connect to RF / DC ground	
4	RF in	DC coupled and 50 ohm matched	
23	Vdd	Power supply voltage Decoupling and bypass caps required	
16	RF out	DC blocked and 50 ohm matched	
9	Vgg	Power supply voltage Decoupling and bypass caps required	

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Applications Information

Application Circuit



Biasing and Operation

The CMD245C4 is biased with a positive drain supply and positive gate supply. Performance is optimized when the drain voltage is set to +5.0 V. The recommended gate voltage is +3.0 V.

Turn ON procedure:

1. Apply drain voltage V_{dd} and set to +5 V
2. Apply gate voltage V_{gg} and set to +3 V

Turn OFF procedure:

1. Turn off gate voltage V_{gg}
2. Turn off drain voltage V_{dd}

RF power can be applied at any time.

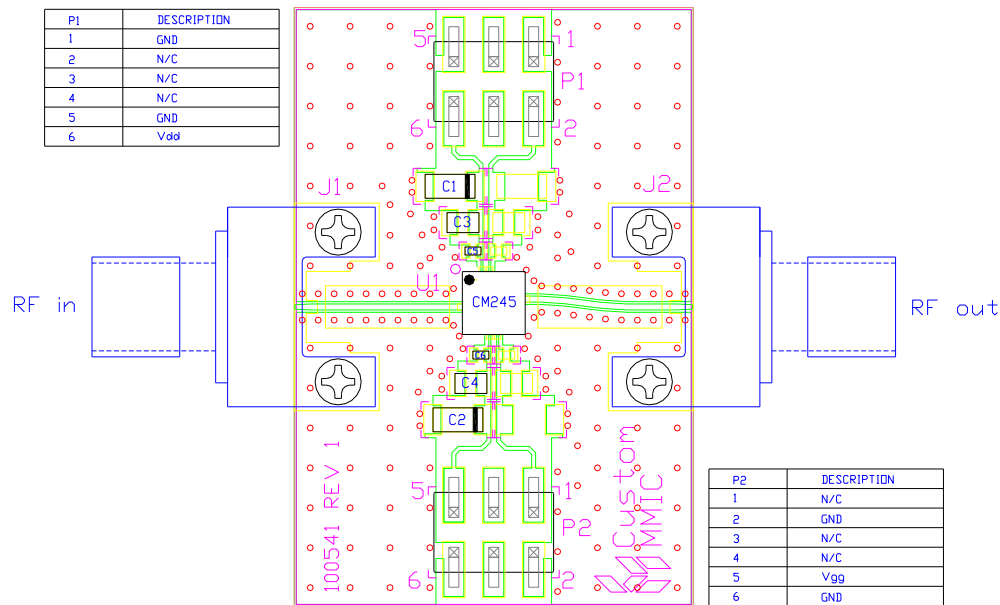
GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

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Applications Information

Evaluation Board

The circuit board shown has been developed for optimized assembly at Custom MMIC. A sufficient number of via holes should be used to connect the top and bottom ground planes. As surface mount processes vary, careful process development is recommended.



Bill of Material

Designator	Value	Description
J1, J2		SMA End Launch Connector
P1, P2		6 Pin Header
C1, C2	0.33 μ F	Capacitor, Tantalum
C3, C4	1000 pF	Capacitor, 0603
C5, C6	100 pF	Capacitor, 0402
U1		CMD245C4 Driver Amplifier
PCB		100541 Evaluation PCB

Please note, all information contained in this data sheet is subject to change without notice.

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